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Practitioner's Docket No.: 782_206

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the application of: Tomohiko SHIBATA, Keiichiro ASAI, Yukinori
NAKAMURA and Mitsuhiro TANAKA

Ser. No.: 10/017,325

Group Art Unit: 2811

Filed: December 14, 2001

Examiner: Junghwa M. Im

Confirmation No.: 8198

For: SEMICONDUCTOR ELEMENT

M.S. After Final
Commissioner for Patents
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CERTIFICATE OF FACSIMILE TRANSMISSION

I hereby certify that this paper is being facsimile transmitted to 703/872-9306 at
the U.S. Patent & Trademark Office on January 10, 2005.


Gina M. Husak

REQUEST FOR RECONSIDERATION

Sir:

The following remarks are in response to the Office Action mailed September 9, 2004
and the Advisory Action mailed December 27, 2004.

1. Claims 1-6, 8 and 10-15 are pending herein. Claims 1-6, 8 and 10-15 were rejected
under §103(a) over Ohba in view of Ogawa. This rejection is respectfully traversed.

Examiner Im and Primary Examiner Nadav are thanked for the courtesies extended to
Applicants' undersigned representative during a telephonic interview on January 6, 2005.
During the interview, Primary Examiner Nadav requested that the undersigned representative
submit written remarks, along with Applicants' Exhibit, reiterating the points discussed
during the interview. Accordingly, the following discussion is a detailed account of the
subject matter discussed during the January 6 telephonic interview with Examiner Im and
Primary Examiner Nadav.

As discussed in the June 14, 2004 Amendment and the December 9, 2004 Request for
Reconsideration, the entireties of which are incorporated herein by reference, and with
reference to Applicants' attached Exhibit, pending independent claim 1 recites a
semiconductor element having an Al-including first nitride on a substrate. The Al-including
first nitride has a crystallinity corresponding to a full width at half maximum (FWHM) X-ray
rocking curve value of 90 seconds or below, and a thickness between 0.5-1000 μm . While a
second nitride is on the first nitride and has a thickness between 0.002-0.1 μm , a Ga-